



Product data sheet

1. Product profile

1.1 General description

Hyperfast power diode in a SOD113 (2-lead TO-220F) plastic package.

1.2 Features and benefits

- Isolated plastic package
- Low reverse recovery current
- **1.3 Applications**
 - Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Low thermal resistance
- Reduces switching losses in associated MOSFET
- Half-bridge/full-bridge switched-mode power supplies
- Half-bridge lighting ballasts

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	-	600	V
I _{F(AV)}	average forward current	square-wave pulse; $\delta = 0.5$; T _h = 47 °C; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	8	A
Static cha	racteristics					
V _F	forward voltage	I _F = 8 A; T _j = 150 °C; see <u>Figure 4</u>	-	1.5	1.85	V
		I _F = 8 A; T _j = 25 °C	-	2	2.9	V
Dynamic of	characteristics					
t _{rr}	reverse recovery time	I _F = 8 A; V _R = 400 V; dI _F /dt = 500 A/μs; T _j = 25 °C; see <u>Figure 5</u>	-	20	-	ns



2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode		
2	А	anode	mb	K — A 001aaa020
mb	n.c.	mounting base; isolated		
			SOD113 (TO-220F)	

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BYC8DX-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113

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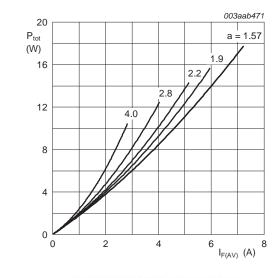
Hyperfast power diode

4. Limiting values

Table 4. Limiting values

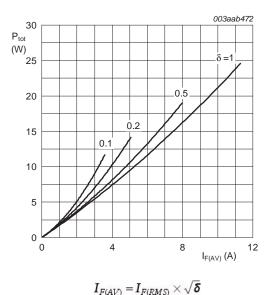
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	600	V
V _{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	square-wave pulse; $\delta = 0.5$; T _h = 47 °C; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	8	А
I _{FRM}	repetitive peak forward current	square-wave pulse; δ = 0.5 ; t_p = 25 $\mu s;$ T_h = 47 °C	-	16	A
I _{FSM}	non-repetitive peak forward current	t _p = 10 ms; sine-wave pulse; T _{j(init)} = 25 ℃	-	55	А
		t_p = 8.3 ms; sine-wave pulse; T _{j(init)} = 25 °C	-	60	А
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C



 $a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$









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5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-h)}	th(j-h) thermal resistance from junction to heatsink	without heatsink compound	-	-	7.2	K/W
u ,		with heatsink compound ; see Figure 3	-	-	5.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air		-	60	-	K/W

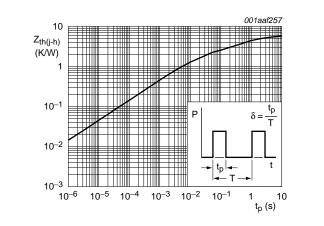


Fig 3. Transient thermal impedance from junction to heatsink as a function of pulse width

6. Isolation characteristics

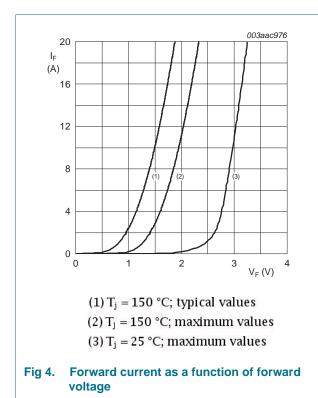
Table 6.	Isolation characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz \leq f \leq 60 Hz; RH \leq 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	f = 1 MHz ; from cathode to external heatsink	-	10	-	pF

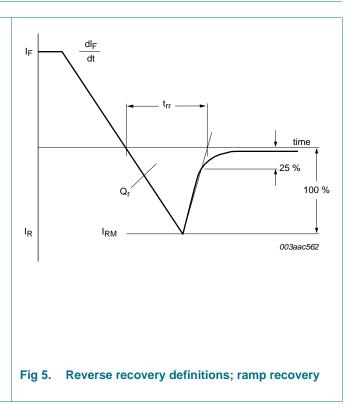
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7. Characteristics

Parameter teristics	Conditions	Min	Typ		
teristics			Тур	Max	Unit
forward voltage	I _F = 8 A; T _j = 150 °C; see <u>Figure 4</u>	-	1.5	1.85	V
	I _F = 8 A; T _j = 25 °C	-	2	2.9	V
reverse current	V _R = 500 V; T _j = 100 °C	-	1.1	3	mA
	V _R = 600 V	-	9	40	μA
racteristics					
recovered charge	$I_F = 1 \text{ A}; V_R = 100 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s}$	-	13	-	nC
reverse recovery time	$I_F = 8 \text{ A}; V_R = 400 \text{V}; \text{d}_F/\text{d}t = 500 \text{A}/\mu\text{s}; \\ \text{T}_j = 100 ^\circ\text{C}$	-	32	40	ns
	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}$	-	30	52	ns
	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ see } Figure 5$	-	20	-	ns
peak reverse recovery current	$\label{eq:IF} \begin{array}{l} I_F = 10 \text{ A}; \text{V}_\text{R} = 400 \text{ V}; \text{d}I_\text{F}/\text{d}t = 500 \text{ A}/\mu\text{s}; \\ T_j = 100 \ ^\circ\text{C} \end{array}$	-	9.5	12	А
	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 50 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}$	-	1.5	5.5	А
forward recovery voltage	$I_F = 10 \text{ A}; \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s}; T_j = 25 \text{ °C};$ see Figure 6	-	8	10	V
	reverse current acteristics recovered charge reverse recovery time peak reverse recovery current forward recovery	$\hline I_{F} = 8 \text{ A}; T_{j} = 25 \text{ °C}$ reverse current $V_{R} = 500 \text{ V}; T_{j} = 100 \text{ °C}$ $V_{R} = 600 \text{ V}$ Facteristics $\hline \text{recovered charge} \qquad I_{F} = 1 \text{ A}; V_{R} = 100 \text{ V}; dI_{F}/dt = 100 \text{ A/}\mu\text{s}$ $\hline \text{reverse recovery time} \qquad I_{F} = 8 \text{ A}; V_{R} = 400 \text{ V}; dI_{F}/dt = 500 \text{ A/}\mu\text{s};$ $T_{j} = 100 \text{ °C}$ $I_{F} = 1 \text{ A}; V_{R} = 30 \text{ V}; dI_{F}/dt = 500 \text{ A/}\mu\text{s};$ $T_{j} = 25 \text{ °C}$ $I_{F} = 8 \text{ A}; V_{R} = 400 \text{ V}; dI_{F}/dt = 500 \text{ A/}\mu\text{s};$ $T_{j} = 25 \text{ °C}$ $I_{F} = 8 \text{ A}; V_{R} = 400 \text{ V}; dI_{F}/dt = 500 \text{ A/}\mu\text{s};$ $T_{j} = 25 \text{ °C}; \text{ see Figure 5}$ $\hline \text{peak reverse recovery} \qquad I_{F} = 10 \text{ A}; V_{R} = 400 \text{ V}; dI_{F}/dt = 500 \text{ A/}\mu\text{s};$ $T_{j} = 100 \text{ °C}$ $I_{F} = 8 \text{ A}; V_{R} = 400 \text{ V}; dI_{F}/dt = 500 \text{ A/}\mu\text{s};$ $T_{j} = 100 \text{ °C}$ $I_{F} = 8 \text{ A}; V_{R} = 400 \text{ V}; dI_{F}/dt = 500 \text{ A/}\mu\text{s};$ $T_{j} = 125 \text{ °C}$ $forward recovery \qquad I_{F} = 10 \text{ A}; dI_{F}/dt = 100 \text{ A/}\mu\text{s}; T_{j} = 25 \text{ °C};$	$\label{eq:reverse current} \begin{array}{c} I_{F} = 8 \mbox{ A; } T_{j} = 25 \mbox{ °C } & - & - & - & - & - & - & - & - & - &$	$\begin{tabular}{ l_F = 8 A; T_j = 25 \ ^{\circ}C & - & 2 \\ \hline l_F = 8 A; T_j = 25 \ ^{\circ}C & - & 1.1 \\ \hline V_R = 500 \ V; T_j = 100 \ ^{\circ}C & - & 1.1 \\ \hline V_R = 600 \ V & - & 9 \\ \hline \end{tabular}$	$\begin{tabular}{ l l l l l l l l l l l l l l l l l l l$

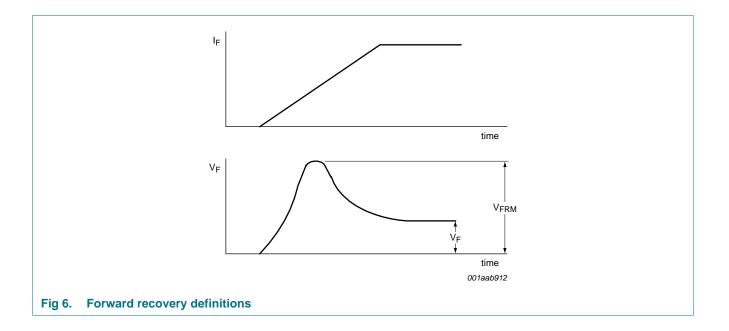




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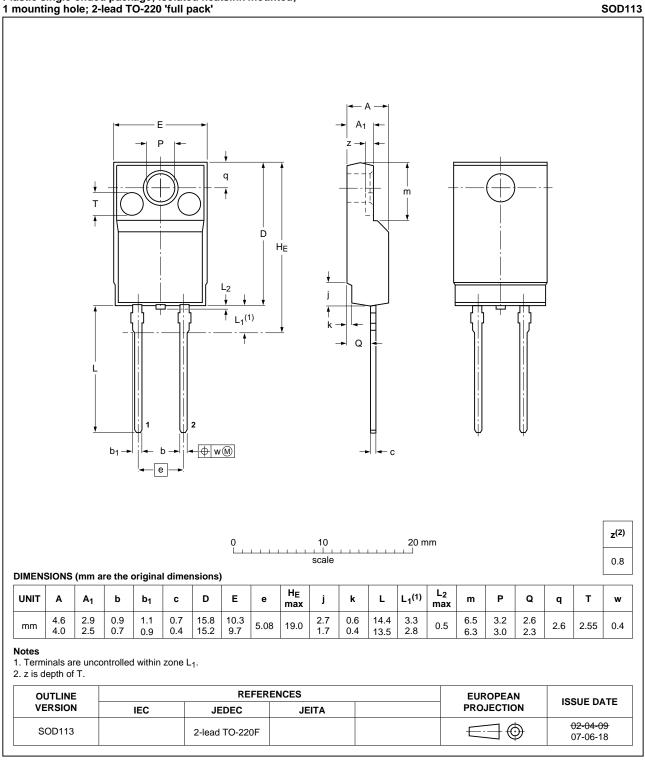
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Package outline 8.



Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 'full pack'

Fig 7. Package outline SOD113 (TO-220F)

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9. Revision history

Table 8. Revisi	Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
BYC8DX-600 v.1	20101227	Product data sheet	-	-			

10. Legal information

10.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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